

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/617,793	07/14/2003	Yoshiharu Anda	2003_0955A	4076
•	7590 . 05/24/2004		EXAMINER	
WENDEROTH, LIND & PONACK, L.L.P. 2033 K STREET N. W.			PHAM, THANH V	
SUITE 800 WASHINGTON, DC 20006-1021		· · · · · · · · · · · · · · · · · · ·	ART UNIT	PAPER NUMBER
			2823	
			. DATE MAILED: 05/24/2004	• •

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)
	10/617,793	ANDA ET AL.
Office Action Summary	Examiner	Art Unit
	Thanh V Pham	2823
The MAILING DATE of this communication appeared for Reply	ears on the cover sheet with the	correspondence address
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply of NO period for reply is specified above, the maximum statutory period we failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	6(a). In no event, however, may a reply be till within the statutory minimum of thirty (30) day ill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	mely filed ys will be considered timely. the mailing date of this communication.
Status		
Responsive to communication(s) filed on 11 Ma This action is FINAL. 2b) ☑ This Since this application is in condition for allowan closed in accordance with the practice under Expensive to communication(s) filed on 11 Ma This action is FINAL. 2b) ☑ This	action is non-final. ce except for formal matters, pr	
Disposition of Claims		
 4) Claim(s) 1-12 is/are pending in the application. 4a) Of the above claim(s) 7-12 is/are withdrawn 5) Claim(s) is/are allowed. 6) Claim(s) 1-6 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/or 	*	
Application Papers		
9) The specification is objected to by the Examiner 10) The drawing(s) filed on is/are: a) access Applicant may not request that any objection to the deplacement drawing sheet(s) including the correction 11) The oath or declaration is objected to by the Examiner 11.	pted or b) objected to by the rawing(s) be held in abeyance. Second is required if the drawing(s) is ob	e 37 CFR 1.85(a). jected to. See 37 CFR 1.121(d).
Priority under 35 U.S.C. § 119		
a) Acknowledgment is made of a claim for foreign part a) All b) Some * c) None of: 1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the priority application from the International Bureau * See the attached detailed Office action for a list of	have been received. have been received in Applicati ty documents have been receive (PCT Rule 17.2(a)).	on No ed in this National Stage
		•
Attachment(s)		
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 09/15/03.	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:	•

Application/Control Number: 10/617,793

Art Unit: 2823

DETAILED ACTION

Election/Restrictions

1. Applicant's election of Group I, claims 1-6, in Paper filed 03/11/04 is acknowledged. Because applicant did not distinctly and specifically point out the supposed errors in the restriction requirement, the election has been treated as an election without traverse (MPEP § 818.03(a)).

Specification

2. The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed.

The following title is suggested: Schottky Junction Electrode Made of Lanthanum Hexaboride.

Drawings

3. Figures 1 and 2 should be designated by a legend such as --Prior Art-- because only that which is old is illustrated. See MPEP § 608.02(g). A proposed drawing correction or corrected drawings are required in reply to the Office action to avoid abandonment of the application. The objection to the drawings will not be held in abeyance.

Claim Rejections - 35 USC § 103

- 4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the

Application/Control Number: 10/617,793

Art Unit: 2823

invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

5. Claims 1-6 are rejected under 35 U.S.C. 103(a) as being unpatentable over applicant's admitted prior art in combination with Weitzel et al. US 5,693,969.

Applicant's admitted prior art as in fig. 1 and in pages 2-3 of the specification discloses substantially the same GaAs PHEMT as claimed but lacks the gate electrode made of LaB₆. (The known GaAs PHEMT comprises a Schottky layer 126; and a Schottky electrode 130 that is formed on the Schottky layer and has a Schottky contact with the Schottky layer' wherein the Schottky layer is composed of a compound semiconductor including In and P (InGaP, *re claim 2*), and the portion of the Schottky electrode that touches the Schottky layer is composed of material whose main constituents are not disclosed.)

Re claims 3 and 5, the Weitzel et al. reference discloses a Schottky gate 16 made of LaB₆ (col. 1, line 60 and col. 3, lines 25-27) that helps increasing the breakdown voltage of a FET, does not affect the frequency response, the transconductance and does not require the use of a high resistance refractory gate material (col. 1, lines 15-39). Re claims 4 and 6, the applied "technique is suitable for vertical current flow diodes" (col. 1, line 30) and "to the gate of the MESFET" (col. 1, line 17).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to employ the Schottky gate material of Weitzel et al. as the gate electrode of applicant's admitted prior art because the LaB₆ gate would increase the breakdown voltage of a FET without affecting the frequency response and the

Application/Control Number: 10/617,793

Art Unit: 2823

transconductance, and does not require the use of a high resistance refractory gate material.

Conclusion

- 6. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.
- Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thanh V. Pham whose telephone number is 571-272-1866. The examiner can normally be reached on M-T (6:30-5:00).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on 571-272-1855. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

TvP TvP 05/10/04

> Olik Chaudhuri Supervisory Patent Examiner Technology Center 2800

Page 4